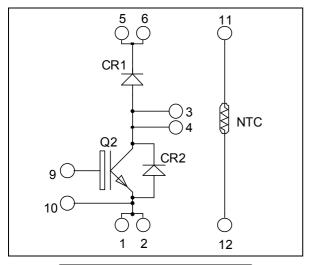
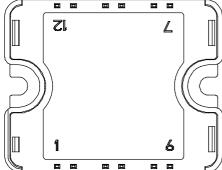


# Boost chopper NPT IGBT Power Module

$$V_{CES} = 1200V$$
  
 $I_{C} = 50A$  @  $Tc = 80$ °C





Pins 1/2; 3/4; 5/6 must be shorted together

#### Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

#### **Features**

- Non Punch Through (NPT) Fast IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

#### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

#### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		1200	V
T	Continuous Collector Current	$T_c = 25^{\circ}C$	75	
$I_{C}$	Continuous Conector Current	$T_c = 80^{\circ}C$	50	Α
$I_{CM}$	Pulsed Collector Current	$T_c = 25$ °C	150	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Maximum Power Dissipation	$T_c = 25^{\circ}C$	312	W
RBSOA	Reverse Bias Safe Operating Area	$T_i = 150^{\circ}C$	100A @ 1200V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



### All ratings @ $T_j = 25$ °C unless otherwise specified

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V$	$T_i = 25^{\circ}C$			250	μA
ICES	Zero Gate Voltage Collector Current	$V_{CE} = 1200V$	$T_{i} = 125^{\circ}C$			500	μΛ
17	Callantan Emittan antonotica Waltern	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		3.2	3.7	V
$V_{\text{CE(sat)}}$	Collector Emitter saturation Voltage	$I_C = 50A$	$T_j = 125$ °C		4.0		v
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1 \text{ mA}$		4.5		6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20 \text{ V}, V_{CE} = 0 \text{ V}$				100	nA

**Dynamic Characteristics** 

·	Characteristic	Test Conditions	1	Min	Typ	Max	Unit
C <sub>ies</sub>	Input Capacitance	$V_{GE} = 0V$			3450		
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$			330		pF
$C_{res}$	Reverse Transfer Capacitance	f = 1 MHz			220		
$Q_{g}$	Total gate Charge	$V_{GS} = 15V$			330		
$Q_{ge}$	Gate – Emitter Charge	$V_{Bus} = 600V$			35		nC
$Q_{gc}$	Gate – Collector Charge	$I_C = 50A$			200		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	hing (25°C)		35		
$T_{\rm r}$	Rise Time	$V_{GE} = 15V$ $V_{Bus} = 600V$ $I_{C} = 50A$			65		ns
$T_{d(off)}$	Turn-off Delay Time				320		
$T_{\mathrm{f}}$	Fall Time	$R_G = 5 \Omega$			30		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$			35		
$T_{\rm r}$	Rise Time				65		
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 600\text{V}$ $I_{\text{C}} = 50\text{A}$			360		ns
$T_{\mathrm{f}}$	Fall Time	$R_G = 5 \Omega$			40		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_j = 125$ °C		6.9	_	I
$E_{\text{off}}$	Turn-off Switching Energy	$I_{C} = 50A$ $R_{G} = 5 \Omega$	$T_j = 125$ °C		3.05		mJ

**Chopper diode ratings and characteristics** 

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit				
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			1200			V				
Ţ	Maximum Reverse Leakage Current	$V_{R}=1200V$	$T_j = 25$ °C			100	۸				
$I_{RM}$		V <sub>R</sub> -1200 V	$T_{j} = 125^{\circ}C$			500	μA				
$I_F$	DC Forward Current		$Tc = 80^{\circ}C$		60		A				
	Diode Forward Voltage	$I_F = 60A$			2.5	3					
$V_{\mathrm{F}}$		$I_{\rm F} = 120A$		3		V					
		$I_F = 60A$	$T_j = 125$ °C		1.8						
t <sub>rr</sub>	Reverse Recovery Time	$I_F = 60A$ $V_R = 800V$ $di/dt = 200A/\mu s$	$T_j = 25$ °C		265		ns				
ι <sub>rr</sub>	Reverse Recovery Time		-	-	-	$I_{\rm F} = 00A$	$T_{j} = 125^{\circ}C$		350		113
$Q_{rr}$	Reverse Recovery Charge		$T_j = 25$ °C		560		пC				
			$T_{j} = 125^{\circ}C$		2890		iiC				

2 - 7



### Thermal and package characteristics

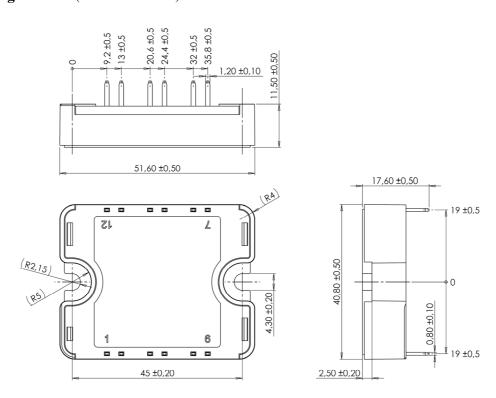
Symbol	Characteristic			Min	Тур	Max	Unit	
$R_{thJC}$	Junction to Case Thermal Resistance		I	GBT		0.4		°C/W
KthJC		D	Diode			0.9		
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V	
$T_{J}$	Operating junction temperature range			-40		150		
$T_{STG}$	Storage Temperature Range			-40		125	°C	
$T_{\rm C}$	Operating Case Temperature				-40		100	
Torque	Mounting torque	To heatsing	ık	M4	2	•	3	N.m
Wt	Package Weight		·	•		•	80	g

### Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_T = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature} \\ R_T: \text{ Thermistor value at T}$$

### SP1 Package outline (dimensions in mm)

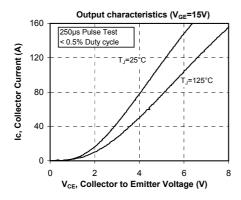


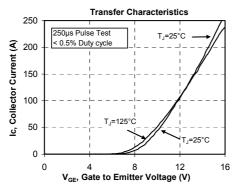
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

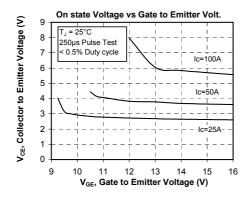
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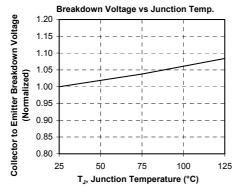


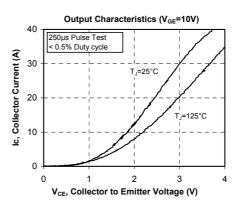
### **Typical Performance Curve**

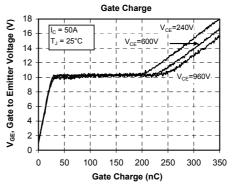


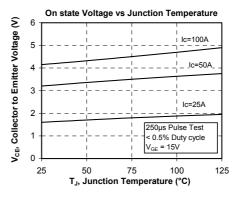


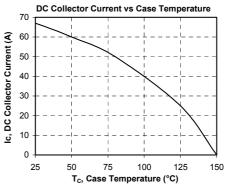




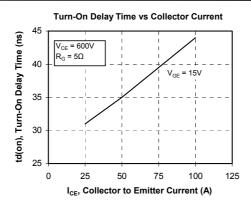


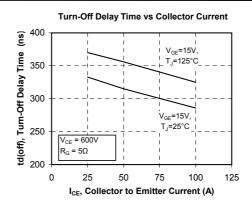


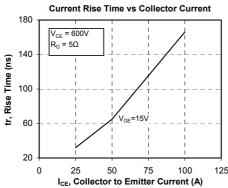


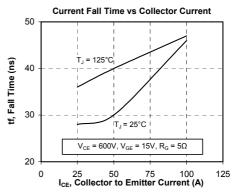


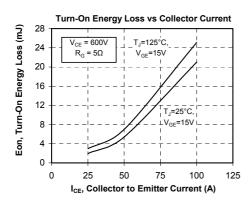


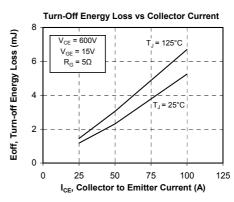


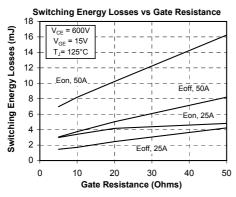


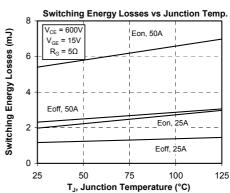




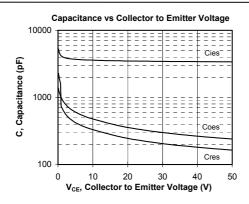


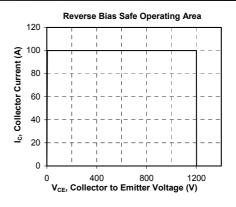


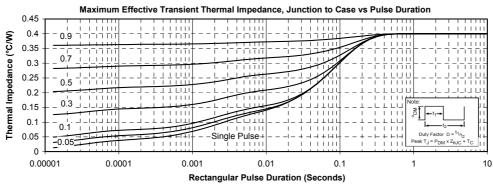


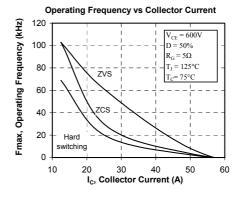












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